

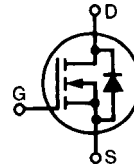
# HiPerFET™ Power MOSFETs Q-Class

**IXFH 20N60Q**  
**IXFT 20N60Q**

$V_{DSS} = 600 \text{ V}$   
 $I_{D25} = 20 \text{ A}$   
 $R_{DS(on)} = 0.35 \text{ } \Omega$

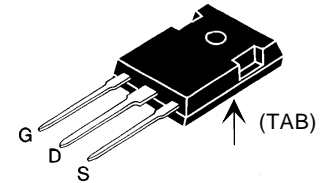
$t_{rr} \leq 250\text{ns}$

N-Channel Enhancement Mode  
Avalanche Rated, High dv/dt,  
Low Gate Charge and Capacitances

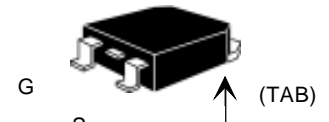


Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	600	V
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GS} = 1 \text{ M}\Omega$	600	V
$V_{GS}$	Continuous	$\pm 30$	V
$V_{GSM}$	Transient	$\pm 40$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	20	A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$	80	A
$I_{AR}$	$T_C = 25^\circ\text{C}$	20	A
$E_{AR}$	$T_C = 25^\circ\text{C}$	30	mJ
$E_{AS}$	$T_C = 25^\circ\text{C}$	1.5	J
dv/dt	$I_S \leq I_{DM}$ , $di/dt \leq 100 \text{ A}/\mu\text{s}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ\text{C}$ , $R_G = 2 \text{ } \Omega$	15	V/ns
$P_D$	$T_C = 25^\circ\text{C}$	300	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$T_L$	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
$M_d$	Mounting torque	1.13/10	Nm/lb.in.
Weight	TO-247 AD	6	g
	TO-268	4	g

### TO-247 AD (IXFH)



### TO-268 (IXFT) Case Style



G = Gate  
S = Source  
D = Drain  
TAB = Drain

### Features

- IXYS advanced low gate charge process
- International standard packages
- Low gate charge and capacitance
  - easier to drive
  - faster switching
- Low  $R_{DS(on)}$
- Unclamped Inductive Switching (UIS) rated
- Molding epoxies meet UL 94 V-0 flammability classification

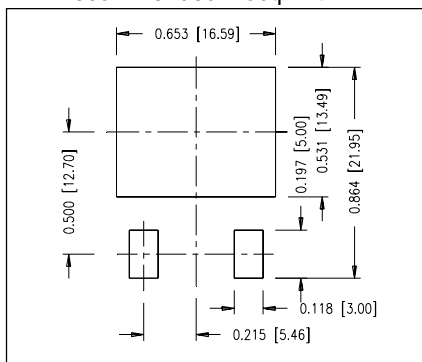
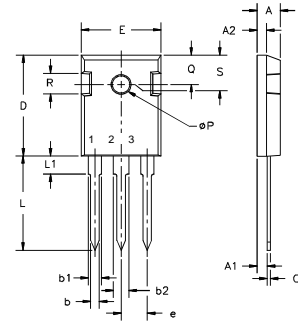
### Advantages

- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$V_{DSS}$	$V_{GS} = 0 \text{ V}$ , $I_D = 250 \text{ } \mu\text{A}$	600		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 4 \text{ mA}$	2.0		V
$I_{GSS}$	$V_{GS} = \pm 30 \text{ V}_{DC}$ , $V_{DS} = 0$			$\pm 100 \text{ nA}$
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $T_J = 25^\circ\text{C}$			25 $\mu\text{A}$
	$V_{GS} = 0 \text{ V}$ , $T_J = 125^\circ\text{C}$			1 mA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$ , $I_D = 0.5 I_{D25}$ Pulse test, $t \leq 300 \text{ } \mu\text{s}$ , duty cycle $d \leq 2 \%$			0.35 $\Omega$

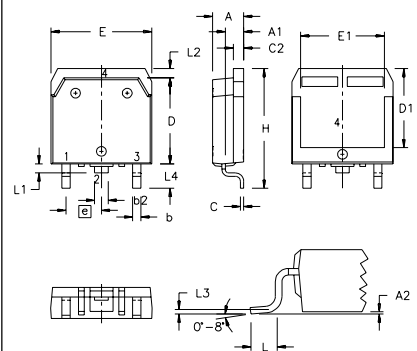
Symbol	Test Conditions	Characteristic Values		
		(T <sub>J</sub> = 25°C, unless otherwise specified)		
		Min.	Typ.	Max.
<b>g<sub>fs</sub></b>	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 0.5 I <sub>D25</sub> , pulse test	10	20	S
<b>C<sub>iss</sub></b>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 25 V, f = 1 MHz		3300	pF
<b>C<sub>oss</sub></b>			410	pF
<b>C<sub>rss</sub></b>			130	pF
<b>t<sub>d(on)</sub></b>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 0.5 V <sub>DSS</sub> , I <sub>D</sub> = 0.5 I <sub>D25</sub> R <sub>G</sub> = 1.5 Ω (External)		20	ns
<b>t<sub>r</sub></b>			20	ns
<b>t<sub>d(off)</sub></b>			45	ns
<b>t<sub>f</sub></b>			20	ns
<b>Q<sub>g(on)</sub></b>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 0.5 V <sub>DSS</sub> , I <sub>D</sub> = 0.5 I <sub>D25</sub>		90	nC
<b>Q<sub>gs</sub></b>			20	nC
<b>Q<sub>gd</sub></b>			45	nC
<b>R<sub>thJC</sub></b>			0.42	K/W
<b>R<sub>thCK</sub></b>	(TO-247)		0.25	K/W

Symbol	Test Conditions	Characteristic Values		
		(T <sub>J</sub> = 25°C, unless otherwise specified)		
		min.	typ.	max.
<b>I<sub>S</sub></b>	V <sub>GS</sub> = 0 V			20 A
<b>I<sub>SM</sub></b>	Repetitive; pulse width limited by T <sub>JM</sub>			80 A
<b>V<sub>SD</sub></b>	I <sub>F</sub> = I <sub>S</sub> , V <sub>GS</sub> = 0 V, Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %			1.5 V
<b>t<sub>rr</sub></b>	I <sub>F</sub> = I <sub>S</sub> , -di/dt = 100 A/μs, V <sub>R</sub> = 100 V		0.85	250 ns
<b>Q<sub>RM</sub></b>				8 μC
<b>I<sub>RM</sub></b>				

**Min Recommended Footprint**

**TO-247 AD Outline**


Terminals: 1 - Gate 2 - Drain  
3 - Source Tab - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A <sub>1</sub>	2.2	2.54	.087	.102
A <sub>2</sub>	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b <sub>1</sub>	1.65	2.13	.065	.084
b <sub>2</sub>	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	242	BSC

**TO-268 Outline**


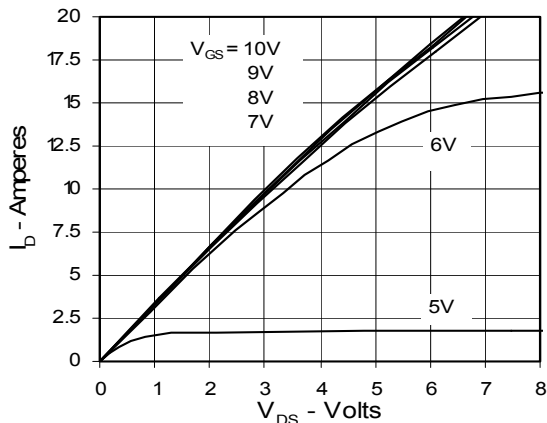
SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

IXYS reserves the right to change limits, test conditions, and dimensions.

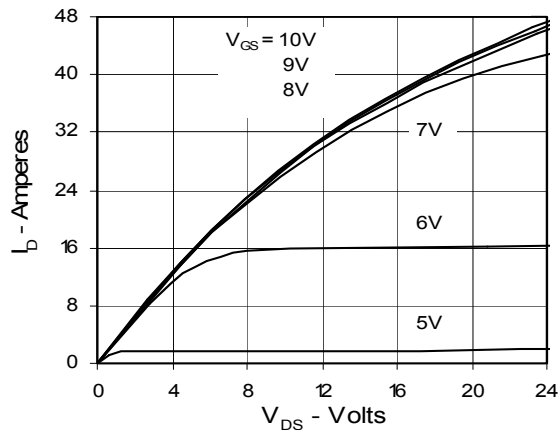
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715 6,306,728B1 6,259,123B1 6,306,728B1  
4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025 6,404,065B1 6,162,665 6,534,343

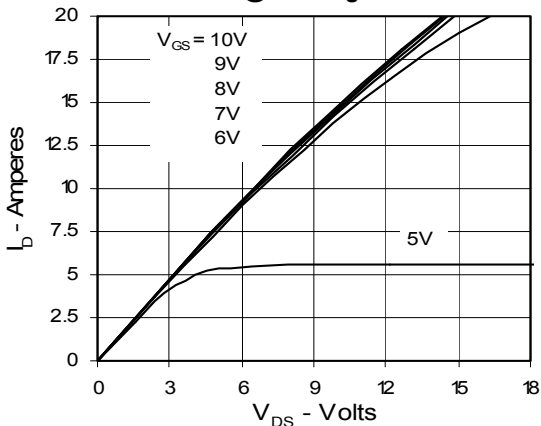
**Fig. 1. Output Characteristics**  
**@ 25 Deg. C**



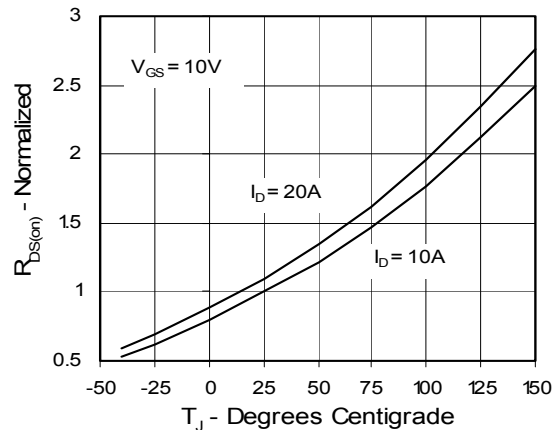
**Fig. 2. Extended Output Characteristics**  
**@ 25 deg. C**



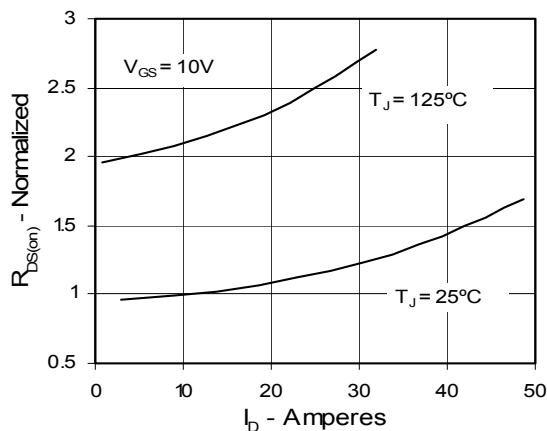
**Fig. 3. Output Characteristics**  
**@ 125 Deg. C**



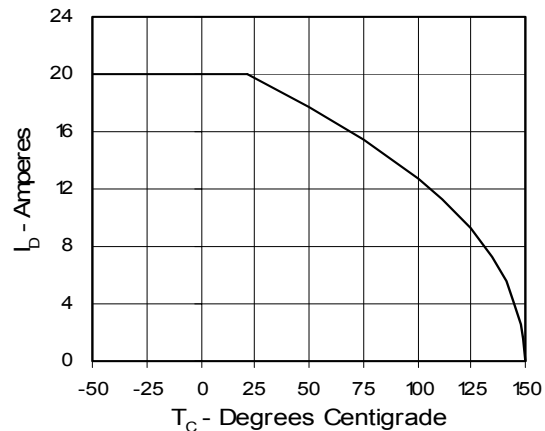
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_{D25}$  Value vs. Junction Temperature**



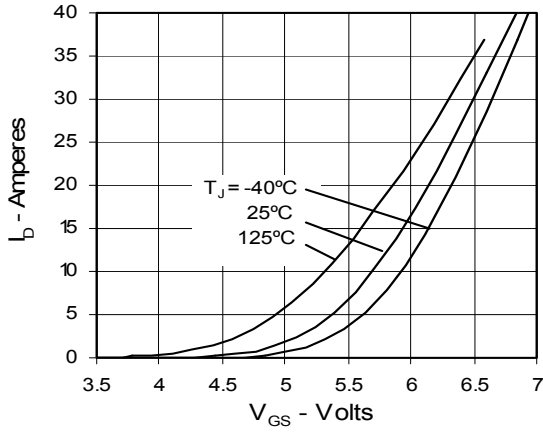
**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_{D25}$  Value vs.  $I_D$**



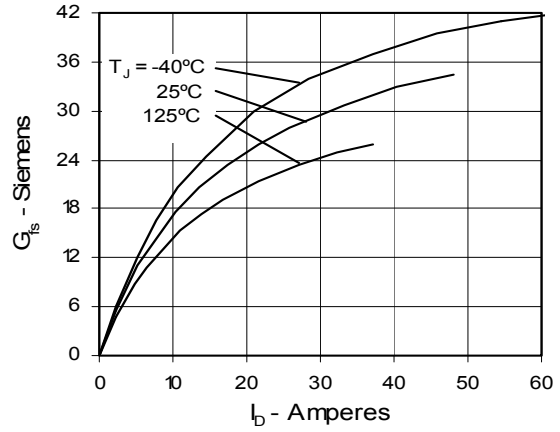
**Fig. 6. Drain Current vs. Case Temperature**



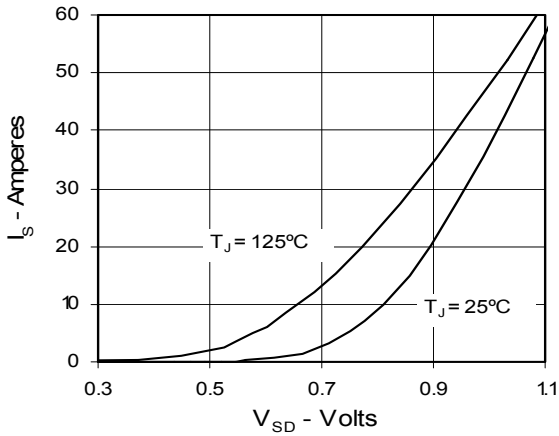
**Fig. 7. Input Admittance**



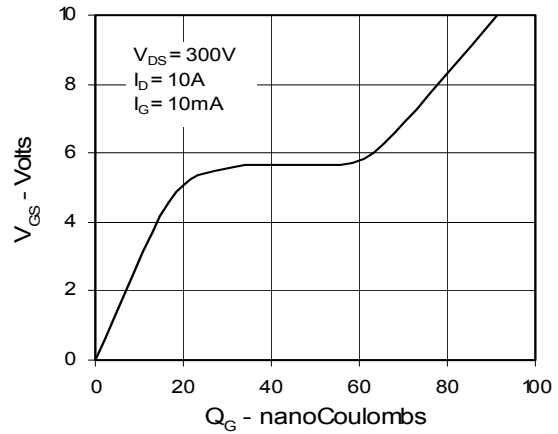
**Fig. 8. Transconductance**



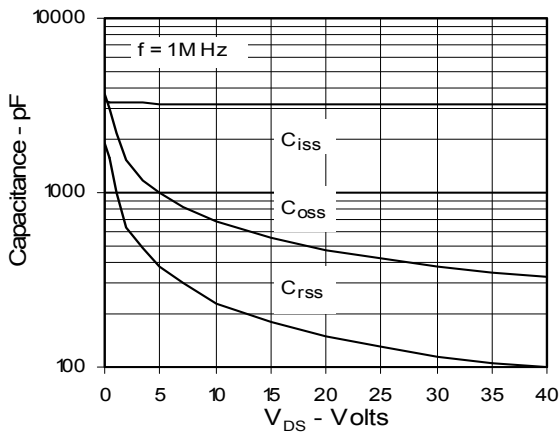
**Fig. 9. Source Current vs. Source-To-Drain Voltage**



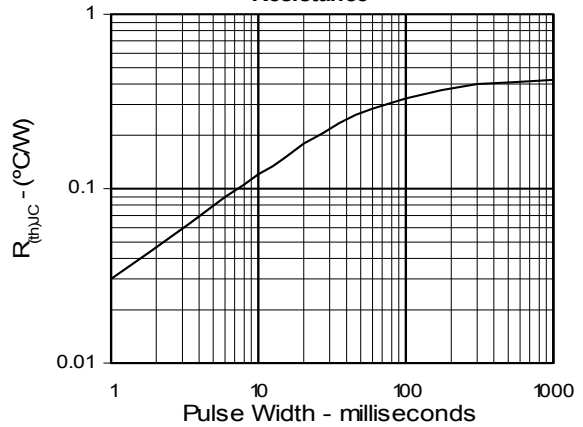
**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Maximum Transient Thermal Resistance**



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